

WE CLAIM:

1. An automatic test equipment (ATE) bidirectional drive channel for transmitting test signals to a device under test (DUT) and receiving signals from the DUT, comprising:

- 5 an input/output line for connection to a DUT,
 a driver circuit connected to apply test signals to said input/output line for application to a DUT,
 a receiver circuit connected to said input/output line to receive signals produced by a DUT, said receiver circuit having an associated capacitance, and
10 a first passive matching network connected to said line to at least partially compensate for said receiver circuit capacitance.

2. The ATE drive channel of claim 1, said first passive matching circuit comprising a T-coil circuit.

3. The ATE drive channel of claim 2, wherein said driver and receiver circuits are implemented on a common layer of an integrated circuit (IC), and said T-coil circuit includes inductors that are implemented in a separate layer of said IC that is spaced from said common layer by at least a dielectric layer.
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4. The ATE drive channel of claim 3, further comprising a flip-chip bump having an associated redistribution layer at the same level as said T-coil inductors.

5. The ATE drive channel of claim 1, said driver circuit comprising the combination of a current-mode driver having an associated capacitance and a voltage-mode driver, said receiver circuit comprising a compara-

5 tor circuit for comparing a signal received from a DUT to
a reference, further comprising a second passive matching
network connected in series with said first passive
matching network to at least partially compensate for
said current-mode driver capacitance.

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6. The ATE drive channel of claim 5, said first and
second passive matching circuits comprising respective T-
coil circuits.

5 7. An automatic test equipment (ATE) receive chan-
nel for receiving signals from a device under test (DUT),
comprising:

an output line for connection to a DUT,

10 at least one receiver circuit connected to said
output line to receive signals produced by a DUT, said
receiver circuit having an associated capacitance, and

a passive matching network connected to said
line to at least partially compensate for said receiver
capacitance.

8. The ATE receive channel of claim 7, said pas-
sive matching circuit comprising a T-coil circuit.

9. The ATE receive channel of claim 8, wherein
said receiver circuit is implemented on one layer of an
integrated circuit (IC), and said T-coil circuit includes
inductors that are implemented in a separate layer of
5 said IC that is spaced from said first layer by at least
a dielectric layer.

10. The ATE receive channel of claim 9, further
comprising a flip-chip bump having an associated redis-

10 tribution layer at the same level as said T-coil induc-
tors.

11. A capacitance-compensated circuit package, com-
prising:

 an integrated circuit (IC) structure that in-
cludes a circuit layer with an associated capacitance,
5 a dielectric layer over said circuit layer,
 a T-coil circuit over said dielectric layer, and
 electrically conductive connectors extending
through said dielectric layer to connect said T-coil cir-
cuit to said circuit layer so that said T-coil circuit at
10 least partially compensates said capacitance.

12. The circuit package of claim 11, further com-
prising a metallization network overlying said circuit
layer and making electrical contact therewith through a
second dielectric layer, said T-coil circuit connected to
5 said circuit layer via said metallization network.

13. The circuit package of claim 12, further com-
prising a flip-chip bump connected to said circuit layer
and having an associated redistribution layer at the same
level as said T-coil inductors.

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14. A method of compensating for capacitance in an
integrated circuit (IC), comprising:

 fabricating an IC package having an electrical
circuit with an unwanted capacitance,
5 providing a first dielectric layer over said IC
package,

 forming a T-coil circuit with inductors that are
on said first dielectric layer, and

connecting said T-coil circuit through said
10 first dielectric layer to said electrical circuit to at
least partially compensate said capacitance.

15. The method of claim 14, wherein said T-coil
circuit is formed and connected to said electrical cir-
cuit by forming openings through said dielectric layer,
depositing a conductive material through said openings,
5 and establishing said T-coil circuit on said dielectric
layer in contact with said conductive material.

16. The method of claim 15, wherein said IC package
is fabricated with a second dielectric layer over said
electrical circuit, and a metallization network on said
second dielectric layer and extending through said second
5 dielectric layer to contact said electrical circuit, and
wherein said T-coil circuit is connected to said electri-
cal circuit via said metallization network.

17. The method of claim 16, wherein said IC package
is fabricated with a passivation layer over said second
dielectric layer and metallization network, openings are
formed through said passivation layer in registration
5 with said first dielectric layer openings, and said con-
ductive material is deposited through said openings in
both the first dielectric and passivation layers.

18. The method of claim 14, said electrical circuit
comprising a bi-directional automatic test equipment
(ATE) drive channel having a driver circuit connected to
generate test signals for a device under test (DUT) and a
5 receiver circuit for receiving signals generated by a
DUT, said T-coil circuit comprising a first T-coil cir-

cuit that at least partially compensates for capacitance associated with said receiver circuit.

19. The method of claim 18, said driver circuit comprising the combination of a current mode driver having an associated capacitance and a voltage-mode driver, said receiver circuit comprising a comparator circuit for
5 comparing a signal received from a DUT to a reference, further comprising forming a second T-coil circuit on said dielectric layer and connecting said second T-coil circuit through said dielectric layer to at least partially compensate the capacitance associated with said
10 current-mode driver.

20. A capacitance-compensated circuit package, comprising:

a substrate,

an electrical circuit layer on said substrate,
5 said electrical circuit layer having an associated capacitance;

a first dielectric layer over said circuit layer,

10 a second dielectric layer over said first dielectric layer,

a T-coil circuit having inductors in said second dielectric layer,

a flip-chip bump over said second dielectric layer, and

15 a redistribution layer for said flip-chip bump in said second dielectric layer,

said T-coil circuit and redistribution layer connected to respective portions of said electrical circuit layer through said first dielectric layer, with said
20 T-coil circuit at least partially compensating said ca-

pacitance, and said flip-chip bump connected to said redistribution layer.

21. The circuit package of claim 20, further comprising a metallization network overlying said circuit layer and making electrical contact therewith through a further dielectric layer, said T-coil circuit and redistribution layer connected to said circuit layer via said metallization network.